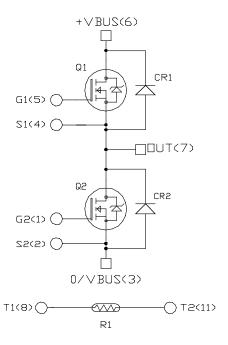
# MSCSM120AM31CTBL1NG

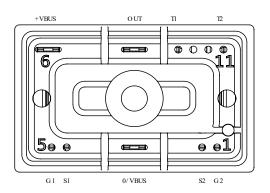
## **Phase Leg SiC MOSFET Power Module**

### **Product Overview**

The MSCSM120AM31CTBL1NG device is a phase leg 1200 V/79 A silicon carbide (SiC) MOSFET power module.







All ratings at T<sub>J</sub> = 25 °C, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

#### **Features**

The following are the key features of MSCSM120AM31CTBL1NG device:

- · SiC Power MOSFET
  - Low R<sub>DS(on)</sub>
  - High speed switching
- · SiC Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature independent switching behavior
  - Positive temperature coefficient on V<sub>F</sub>
- Very low stray inductance
- Ultra-low weight and profile
- Kelvin source for easy drive
- Si<sub>3</sub>N<sub>4</sub> substrate with thick copper for improved thermal performance
- Internal thermistor for temperature monitoring
- Extended temperature range

#### **Benefits**

The following are the benefits of MSCSM120AM31CTBL1NG device:

- High efficiency converter
- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-heatsink thermal resistance
- Low profile
- RoHS Compliant
- Solderable terminals both for power and signal for easy PCB mounting
- Very integrated power conversion system

## **Application**

The following are the applications of MSCSM120AM31CTBL1NG device:

- High reliability power systems
- High Efficiency AC/DC and DC/AC converters
- Motor control

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## 1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120AM31CTBL1NG device.

### 1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM120AM31CTBL1NG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
V <sub>DSS</sub>	Drain-Source voltage		1200	V
I <sub>D</sub>	Continuous drain current	T <sub>H</sub> = 25 °C	79	Α
		T <sub>H</sub> = 80 °C	63	
I <sub>DM</sub>	Pulsed drain current		160	
V <sub>GS</sub>	Gate-Source voltage		-10/25	V
R <sub>DS(on)</sub>	Drain-Source ON resistance		31	mΩ
P <sub>D</sub>	Power dissipation	T <sub>H</sub> = 25 °C	310	W

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM120AM31CTBL1NG device.

**Table 1-2. Electrical Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 1200 V		_	10	100	μΑ
R <sub>DS(on)</sub>	Drain-Source on	V <sub>GS</sub> = 20 V	T <sub>J</sub> = 25 °C	_	25	31	mΩ
	resistance	I <sub>D</sub> = 40 A	T <sub>J</sub> = 175 °C	_	40	_	
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{GS} = V_{DS}$ ; $I_D = 1 \text{ mA}$		1.8	2.8	_	V
I <sub>GSS</sub>	Gate–Source leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V		_	_	150	nA

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM120AM31CTBL1NG device.

**Table 1-3. Dynamic Characteristics** 

Symb ol	Characteristic	Test Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	Input capacitance	V <sub>GS</sub> = 0 V		_	3020	_	pF
C <sub>oss</sub>	Output capacitance	V <sub>DS</sub> = 1000 V f = 1 MHz		_	270	_	
C <sub>rss</sub>	Reverse transfer capacitance			_	25	_	
$Q_g$	Total gate charge	V <sub>GS</sub> = -5 V/20 V		_	232	_	nC
Q <sub>gs</sub>	Gate-Source charge	V <sub>Bus</sub> = 800 V I <sub>D</sub> = 40 A		-	41	_	
$Q_{gd}$	Gate-Drain charge	_		_	50	_	
T <sub>d(on)</sub>	Turn-on delay time	V <sub>GS</sub> = -5 V/20 V		_	30	_	ns
T <sub>r</sub>	Rise time	V <sub>Bus</sub> = 600 V		_	30	_	
T <sub>d(off)</sub>	Turn-off delay time	I <sub>D</sub> = 50 A		_	50	_	
T <sub>f</sub>	Fall time	$R_{Gon} = 8 \Omega$ $R_{Goff} = 4.7 \Omega$		_	25	_	
E <sub>on</sub>	Turn-on energy	V <sub>GS</sub> = -5 V/20 V	T <sub>J</sub> = 150 °C	_	0.99	_	mJ
E <sub>off</sub>	Turn-off energy	$V_{Bus}$ = 600 V $I_{D}$ = 50 A $R_{Gon}$ = 8 $\Omega$ $R_{Goff}$ = 4.7 $\Omega$	T <sub>J</sub> = 150 °C	_	0.66	_	
R <sub>Gint</sub>	Internal gate resistance				0.88	_	Ω
R <sub>thJH</sub>	Junction-to-heatsink	thermal resistance	λ = 3.4 W/mK	_	0.483	_	°C/W

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM120AM31CTBL1NG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
V <sub>SD</sub>	Diode forward voltage	V <sub>GS</sub> = 0 V; I <sub>SD</sub> = 40 A	_	4	_	V
		$V_{GS} = -5 \text{ V}; I_{SD} = 40 \text{ A}$	_	4.2	_	
t <sub>rr</sub>	Reverse recovery time	$I_{SD} = 40 \text{ A}; V_{GS} = -5 \text{ V}$	_	90	_	ns
Q <sub>rr</sub>	Reverse recovery charge	$V_R = 800 \text{ V}; \text{ di}_F/\text{dt} = 1000 \text{ A/}\mu\text{s}$	_	550	_	nC
Irr	Reverse recovery current		_	13.5	_	Α

### 1.2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the SiC diode ratings and characteristics of the MSCSM120AM31CTBL1NG device.

Table 1-5. SiC Diode Ratings and Characteristics (Per SiC Diode)

Symbol	Characteristic	Test Conditi	ons		Min	Тур	Max	Unit
$V_{RRM}$	Peak repetitive reverse vo	oltage			_	_	1200	V
I <sub>RRM</sub>	Reverse leakage current	V <sub>R</sub> = 1200 V		T <sub>J</sub> = 25 °C	_	10	200	μA
				T <sub>J</sub> = 175 °C	_	150	_	
I <sub>F</sub>	DC forward current	_		T <sub>H</sub> = 100 °C	_	30	_	Α
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> = 30 A		T <sub>J</sub> = 25 °C	_	1.5	1.8	V
				T <sub>J</sub> = 175 °C	_	2.1	_	
Q <sub>C</sub>	Total capacitive charge	V <sub>R</sub> = 600 V			_	130	_	nC
С	Total capacitance	f = 1 MHz, V <sub>F</sub>	۹ = 400 ۱	V	_	141	_	pF
		f = 1 MHz, V <sub>R</sub> = 800 V		_	105	_		
R <sub>thJH</sub>	Junction-to-heatsink therr resistance	nal	λ <sub>paste</sub> =	3.4 W/mK	_	0.854	_	°C/W

### 1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM120AM31CTBL1NG device.

Table 1-6. Thermal and Package Characteristics

Symbol	Characteristic				Тур	Max	Unit
V <sub>ISOL</sub>	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz				_	_	V
$T_J$	Operating junction temperature r	ange		<b>-</b> 55	_	175	°C
T <sub>JOP</sub>	Recommended junction temperature under switching conditions			<b>-</b> 55	_	T <sub>Jmax</sub> –25	
T <sub>STG</sub>	Storage case temperature			<b>-</b> 55	_	125	
T <sub>C</sub>	Operating case temperature			<b>-</b> 55	_	125	
Torque	Mounting torque	To heatsink	M4	1.5	_	2	N.m
Wt	Package weight			_	13.5	_	g

The following table lists the temperature sensor NTC of the MSCSM120AM31CTBL1NG device.

Table 1-7. Temperature Sensor NTC

Symbol	Characteristic		Min	Тур	Max	Unit
R <sub>25</sub>	Resistance at 25°C		_	50	_	kΩ
$\Delta R_{25}/R_{25}$	_		_	5	_	%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		_	3952	_	K
ΔΒ/Β	_	T <sub>C</sub> = 100°C	_	4	_	%

$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_{T}: \text{ Thermistor value at T}$$

Note: See APT0406—Using NTC Temperature Sensor Integrated into Power Module for more information.

### 1.4 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM120AM31CTBL1NG device.

Figure 1-1. Junction-to-Heatsink Thermal Impedance

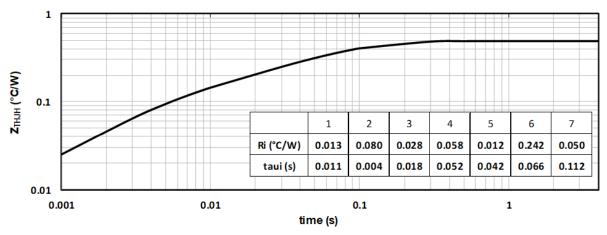


Figure 1-2. Output Characteristics,  $T_J = 25$  °C

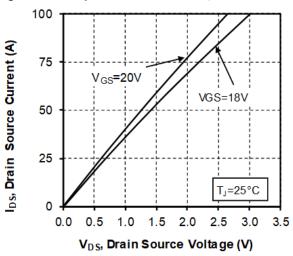


Figure 1-3. Output Characteristics, T<sub>J</sub> = 175 °C

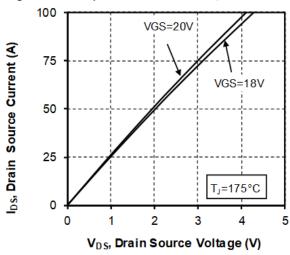


Figure 1-4. Normalized R<sub>DS(on)</sub> vs. Temperature

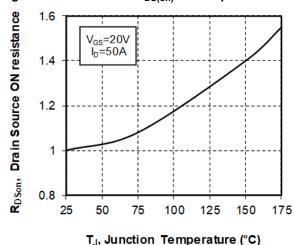


Figure 1-5. Transfer Characteristics

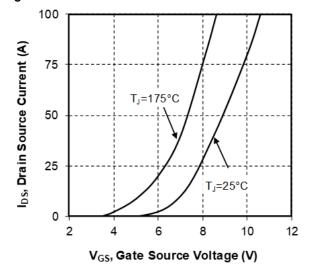


Figure 1-6. Switching Energy vs. Rg

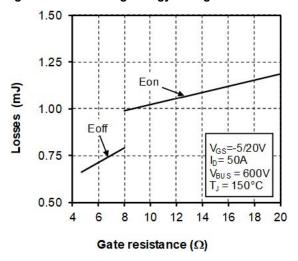


Figure 1-7. Switching Energy vs. Current

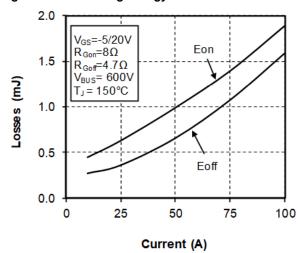


Figure 1-8. Capacitance vs. Drain Source Voltage 10000 Ciss C, Capacitance (pF) 1000 Coss 100 Crss 10 200 400 600 800 1000 V<sub>DS</sub>, Drain source Voltage (V)

T<sub>J</sub> = 25°C  $\mathsf{V}_{\mathsf{GS}},$  Gate to Source Voltage (V)  $I_{D} = 40A$ 15  $V_{DS} = 800V$ 10 5 0 -5 50 100 150 200 250 Gate Charge (nC)

Figure 1-9. Gate Charge vs. Gate Source Voltage

-5 -4.5 -4 -3.5 -3 -2.5 -2 -1.5 -1  $V_{GS} = -5V$ -20

Figure 1-10. Body Diode Characteristics, T<sub>J</sub> = 25 °C

Drain source current (A) V<sub>GS</sub>=0V -40 V<sub>GS</sub>=-2V -60 -80 T<sub>J</sub>=25°C -100 V<sub>DS</sub>, Drain source voltage (V)

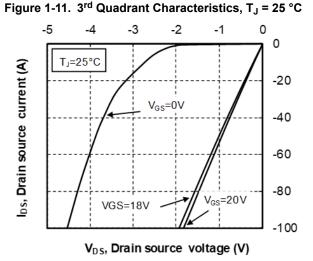
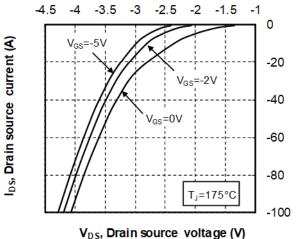


Figure 1-12. Body Diode Characteristics,  $T_J$  = 175 °C Figure 1-13.  $3^{rd}$  Quadrant Characteristics,  $T_J$  = 175 °C



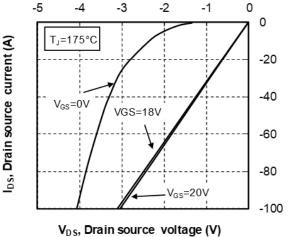
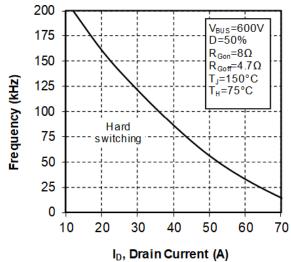


Figure 1-14. Operating Frequency vs Drain Current



#### 1.5 Typical SiC Diode Performance Curves

This section shows the typical SiC diode performance curves of the MSCSM120AM31CTBL1NG device.

Figure 1-15. Junction-to-Heatsink Thermal Impedance

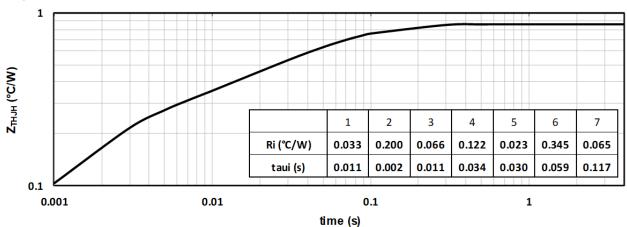


Figure 1-16. Forward Characteristics

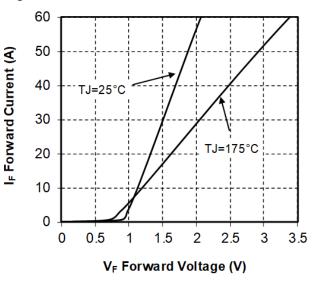
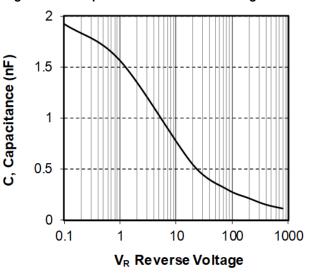


Figure 1-17. Capacitance vs. Reverse Voltage



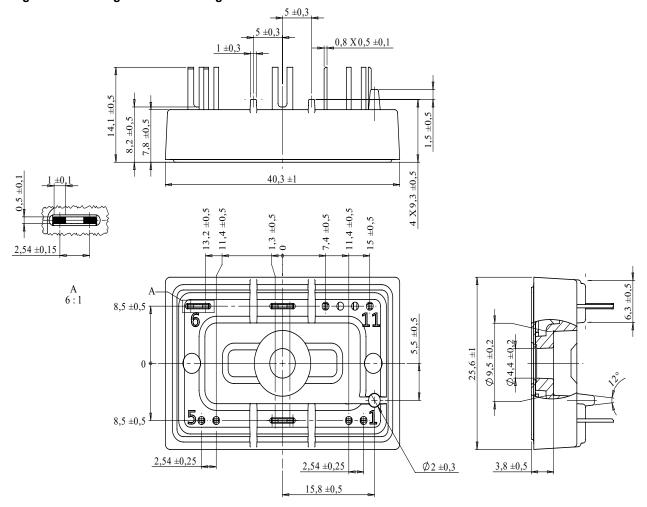
## 2. Package Specifications

The following section shows the package specification of the MSCSM120AM31CTBL1NG device.

### 2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM120AM31CTBL1NG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



## MSCSM120AM31CTBL1NG

**Revision History** 

# 3. Revision History

Revision	Date	Description
Α	07/2021	Initial revision

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